

General Description

The MAX4521/MAX4522/MAX4523 are guad, low-voltage, single-pole/single-throw (SPST) analog switches. On-resistance (100 Ω max) is matched between switches to 4Ω max, and is flat (12Ω max) over the specified signal range. Each switch can handle rail-to-rail analog signals. The off-leakage current is only 1nA at +25°C and 10nA at +85°C.

The MAX4521 has four normally closed (NC) switches, and the MAX4522 has four normally open (NO) switches. The MAX4523 has two NC switches and two NO switches.

These CMOS switches can operate with dual power supplies ranging from ±2V to ±6V or a single supply between +2V and +12V. They are fully specified for single +2.7V operation.

All digital inputs have +0.8V and +2.4V logic thresholds, ensuring TTL/CMOS-logic compatibility when using ±5V or a single +5V supply.

Applications

Battery-Operated Equipment

Data Acquisition

Test Equipment

Avionics

Audio Signal Routing

Networking

Features

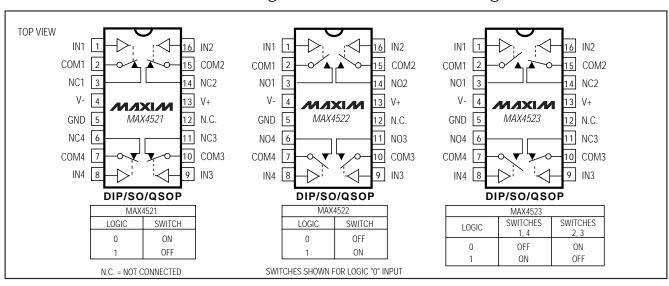
- ±2V to ±6V Dual Supplies
- **♦ 100**Ω Signal Paths with ±5V Supplies
- ♦ Low Power Consumption, <1µW</p>
- ♦ 4 Separately Controlled SPST Switches
- ♦ Rail-to-Rail Signal Handling
- **♦ Pin Compatible with Industry-Standard** DG211/DG212/DG213
- ♦ >2kV ESD Protection per Method 3015.7
- ♦ TTL/CMOS-Compatible Inputs with ±5V or Single +5V Supply

Ordering Information

PART	TEMP. RANGE	PIN-PACKAGE
MAX4521CPE	0°C to +70°C	16 Plastic DIP
MAX4521CSE	0°C to +70°C	16 Narrow SO
MAX4521CEE	0°C to +70°C	16 QSOP
MAX4521C/D	0°C to +70°C	Dice*

Ordering Information continued at end of data sheet.

Pin Configurations/Functional Diagrams/Truth Tables



NIXIN

Maxim Integrated Products 1

^{*}Contact factory for dice specifications.

ABSOLUTE MAXIMUM RATINGS

Voltages Referenced to GND	
V+	0.3V to +13.0V
V	13.0V to +0.3V
V+ to V	0.3V to +13.0V
All Other Pins (Note 1)	(V0.3V) to $(V++0.3V)$
Continuous Current into Any Terminal	±10mA
Peak Current into Any Terminal	
(pulsed at 1ms, 10% duty cycle)	±20mA
ESD per Method 3015.7	

Continuous Power Dissipation ($T_A = +70^{\circ}$	C) (Note 2)
Plastic DIP (derate 10.53mW/°C above	+70°C)842mW
Narrow SO (derate 8.70mW/°C above	+70°C)696mW
QSOP (derate 9.52mW/°C above +70°	C)762mW
CERDIP (derate 10.00mW/°C above +	70°C)800mW
Operating Temperature Ranges	
MAX452_C_E	0°C to +70°C
MAX452_E_E	40°C to +85°C
MAX452_MJE	55°C to +125°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (soldering, 10 sec)	+300°C

- **Note 1:** Signals on NC_, NO_, COM_, or IN_ exceeding V+ or V- are clamped by internal diodes. Limit forward-diode current to maximum current rating.
- Note 2: All leads are soldered or welded to PC boards.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS—Dual Supplies

 $(V+=+4.5V \text{ to } +5.5V, V-=-4.5V \text{ to } -5.5V, T_A=T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted.}$ Typical values are at $T_A=+25^{\circ}C.)$

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP (Note 3)	MAX	UNITS		
ANALOG SWITCH									
Analog Signal Range	V _{COM_} , V _{NO_} , V _{NC_}	(Note 4)	C, E, M	V-		V+	V		
COM_ to NO_, COM_ to NC_	Ron	V+ = 5V, V- = -5V,	+25°C		65	100	Ω		
On-Resistance	NON	$V_{COM} = \pm 3V$, $I_{COM} = 1mA$	C, E, M			125	32		
COM_ to NO_, COM_ to NC_			+25°C		1	4			
On-Resistance Match Between Channels (Note 5)	ΔR _{ON}	V+ = 5V, V- = -5V, $V_{COM} = \pm 3V, I_{COM} = 1mA$	C, E, M			6	Ω		
COM to NO , COM to NC			+25°C		7	12			
On-Resistance Flatness (Note 6)	RFLAT(ON)	V + = 5V, V - = -5V, $V_{COM} = \pm 3V, I_{COM} = 1mA$	C, E, M			15	Ω		
NO NO OTILI	_		+25°C	-1	0.01	1			
NO_, NC_ Off-Leakage Current (Note 7)	INO_(OFF), INC (OFF)	V + = 5.5V, V - = -5.5V, $V_{COM} = \mp 4.5V, V_{N} = \pm 4.5V$	C, E	-10		10	nA		
(Note 1)	INC_(OFF)	VCOM + 4.3 V, VM ±4.3 V	М	-100		100	1		
			+25°C	-1	0.01	1			
COM_ Off-Leakage Current (Note 7)	ICOM_(OFF)	V + = 5.5V, V - = -5.5V, $V_{COM} = \pm 4.5V, V_{N} = \mp 4.5V$	C, E	-10		10	nA		
(Note 7)	_ ,	$VCOM_{=} \pm 4.5V, VN_{=} + 4.5V$	М	-100		100	1		
		.,	+25°C	-2	0.01	2			
COM_ On-Leakage Current (Note 7)	ICOM_(ON)	V + = 5.5V, V - = -5.5V,	C, E	-20		20	nA		
(Note 1)		$V_{COM} = \pm 4.5V$	М	-200		200			

ELECTRICAL CHARACTERISTICS—Dual Supplies (continued)

 $(V+=+4.5V \text{ to } +5.5V, V-=-4.5V \text{ to } -5.5V, T_A=T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted.}$ Typical values are at $T_A=+25^{\circ}C.)$

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP (Note 3)	MAX	UNITS
LOGIC INPUT	I.						
IN_ Input Logic Threshold High	V _{IN_H}		C, E, M		1.6	2.4	V
IN_ Input Logic Threshold Low	V _{IN_L}		C, E, M	0.8	1.6		V
IN_ Input Current Logic High or Low	I _{INH_} , I _{INL_}	V _{IN} _ = 0.8V or 2.4V	C, E, M	-1	0.03	1	μΑ
SWITCH DYNAMIC CHARACTE	RISTICS						
Turn-On Time	+	$V_{COM} = \pm 3V, V_{+} = 4.5V,$	+25°C		45	80	
rum-on time	ton	V- = -4.5V, Figure 1	C, E, M			100	ns
Turn-Off Time	+	$V_{COM} = \pm 3V, V_{+} = 4.5V,$	+25°C		15	30	nc
rum-on nine	toff	$V_{-} = -4.5V$, Figure 1	C, E, M			40	ns
Break-Before-Make Time Delay (MAX4523 Only)	†BBM	V _{COM} = ±3V, V+ = 5.5V, V- = -5.5V, Figure 2	+25°C	5	20		ns
Charge Injection (Note 4)	Q	$C_L = 1nF$, $V_{NO} = 0V$, $R_S = 0\Omega$, Figure 3	+25°C		1	5	рС
NO_, NC_ Off-Capacitance	C _{N_(OFF)}	V _{NO} _ = GND, f = 1MHz, Figure 6	+25°C		2		pF
COM_ Off-Capacitance	CCOM_(OFF)	V _{COM} _ = GND, f = 1MHz, Figure 6	+25°C		2		pF
COM_ On-Capacitance	C _{COM} (ON)	V _{COM} _ = V _{NO} _ = GND, f = 1MHz, Figure 7	+25°C		5		pF
Off-Isolation (Note 8)	V _{ISO}	$R_L = 50\Omega$, $C_L = 15pF$, $V_{N_{-}} = 1V_{RMS}$, $f = 100kHz$, Figure 4	+25°C		< -90		dB
Channel-to-Channel Crosstalk (Note 9)	V _{CT}	$R_L = 50$, $C_L = 15pF$, $V_{N} = 1V_{RMS}$, $f = 100kHz$, Figure 5	+25°C		< -90		dB
POWER SUPPLY							
Power-Supply Range	V+, V-		C, E, M	-6	0.05	6	V
V+ Supply Current	I+	V+ = 5.5V, all V _{IN} _ = 0V or V+	+25°C C, E, M	-1 -1	0.05	1	μA
V- Supply Current	-	V- = -5.5V	+25°C C, E, M	-1 -1	0.05	1	μΑ

ELECTRICAL CHARACTERISTICS—Single +5V Supply

 $(V+=+4.5V \text{ to } +5.5V, V-=0V, T_A=T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted.}$ Typical values are at $T_A=+25^{\circ}C.)$

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP (Note 3)	MAX	UNITS
ANALOG SWITCH							
Analog Signal Range	V _{COM_} , V _{NO_} ,	(Note 4)	C, E, M	0		V+	V
COM_ to NO_, COM_ to NC_	RON	$V + = 4.5V, V_{COM} = 3.5V,$	+25°C		125	200	Ω
On-Resistance	KON	I _{COM} _ = 1mA	C, E, M			250	32
COM_ to NO_, COM_ to NC_ On-Resistance Match Between Channels (Note 5)	ΔR _{ON}	V+ = 5V, V _{COM} _ = 3.5V, I _{COM} _ = 1mA	+25°C C, E, M		2	10	Ω
			+25°C	-1	0.01	1	
NO_, NC_ Off-Leakage Current (Notes 7, 10)	INO_(OFF), INC_(OFF)	$V + = 5.5V$; $V_{COM} = 1V$, $4.5V$; $V_{N} = 4.5V$, $1V$	C, E	-10		10	nA
(Notes 7, 10)	INC_(OFF)	VN 4.5V, 1V	М	-100		100	
	ICOM_(OFF)	V+ = 5.5V; V _{COM} = 1V, 4.5V; V _N = 4.5V, 1V	+25°C	-1	0.01	1	
COM_ Off-Leakage Current (Notes 7, 10)			C, E	-10		10	nA
(Notes 1, 10)			М	-100		100	
COM_ On-Leakage Current (Notes 7, 10)	ICOM_(ON)	V+ = 5.5V; V _{COM} _ = 4.5V, 1V	+25°C	-2	0.01	2	
			C, E,	-20		20	nA
(1001037, 10)			М	-200		200	
LOGIC INPUT							
IN_ Input Logic Threshold High	V _{IN_H}		C, E		1.6	2.4	V
IN_ Input Logic Threshold Low	V _{IN_L}		C, E	0.8	1.6		V
IN_ Input Current Logic High or Low	I _{INH_} , I _{INL_}	V _{IN} _ = 0.8V or 2.4V	C, E	-1	0.03	1	μΑ
SWITCH DYNAMIC CHARACTE	RISTICS	1					
Turn-On Time	tou	$V_{COM} = 3V, V_{+} = 4.5V,$	+25°C		60	100	nc
Turn-On Time	ton	Figure 1	C, E, M			150	- ns
Turn-Off Time	torr	$V_{COM} = 3V, V_{+} = 4.5V,$	+25°C		20	50	nc
Turn-On Time	toff	Figure 1	C, E, M			75	- ns
Break-Before-Make Time Delay (MAX4523 Only)	t _{BBM}	V _{COM} _ = 3V, V+ = 5.5V, Figure 2	+25°C	10	30		ns
Charge Injection (Note 4)	Q	$C_L = 1nF$, $V_{NO} = 0V$, $R_S = 0\Omega$, Figure 3	+25°C		1	5	рС
POWER SUPPLY		1	1				
V. Cupply Cupped	,	V. F.F.V. all.V. OV= V.	+25°C	-1	0.05	1	
V+ Supply Current	I+	$V+ = 5.5V$, all $V_{IN} = 0V$ or $V+$	C, E, M	-1		1	μΑ
V Supply Current	1	V- = OV	+25°C	-1	0.05	1	, , ,
V- Supply Current	I-		C, E, M	-1		1	μΑ

ELECTRICAL CHARACTERISTICS—Single +3V Supply

 $(V+ = +2.7V \text{ to } +3.6V, V- = 0V, T_A = T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted.}$ Typical values are at $T_A = +25^{\circ}\text{C.})$

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP (Note 3)	MAX	UNITS
ANALOG SWITCH							l
Analog Signal Range	V _{COM_} , V _{NO_} , V _{NC_}	(Note 4)	C, E, M	0		V+	V
COM_ to NO_, COM_ to NC_ On-Resistance	Ron	V+ = 2.7V, V _{COM} _ = 1.0V, I _{COM} _ = 0.1mA	+25°C C, E, M		260	500 600	Ω
LOGIC INPUT							
IN_ Input Logic Threshold High	V _{IN_H}		C, E		1.6	2.4	V
IN_ Input Logic Threshold Low	V _{IN_L}		C, E	0.8	1.6		V
IN_ Input Current Logic High or Low	I _{INH_} , I _{INL_}	V _{IN} _ = 0.8V or 2.4V	C, E	-1	0.03	1	μА
SWITCH DYNAMIC CHARACTE	RISTICS (Note 4)						
Turn-On Time	ton	V _{COM} _ = 1.5V, V+ = 2.7V, Figure 1	+25°C		120	250	ns
Turr-On Time			C, E, M			300	113
Turn-Off Time	t _{OFF}	$V_{COM} = 1.5V, V + = 2.7V,$	+25°C		40	80	ns
Tam on Time	·OFF	Figure 1	C, E, M			100	113
Break-Before-Make Time Delay (MAX4523 Only)	†BBM	V _{COM} _ = 1.5V, V+ = 3.6V, Figure 2	+25°C	15	50		ns
Charge Injection	Q	$C_L = 1nF$, $V_{NO} = 0V$, $R_S = 0\Omega$, Figure 3	+25°C		0.5	5	рС
POWER SUPPLY	1	I					ı
V+ Supply Current	+	$V_{+} = 3.6V$, all $V_{IN} = 0V$ or V_{+}	+25°C	-1	0.05	1	μΑ
v + Supply Current	1+	V = - 3.0V, all VIN 0V 0I V+	C, E, M	-1		1	μΑ
V- Supply Current	-	V- = 0V	+25°C	-1	0.05	1	μA
Cappiy Current	I=		C, E, M	-1		1	μ, τ

Note 3: The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.

Note 4: Guaranteed by design.

Note 5: $\Delta R_{ON} = \Delta R_{ON(MAX)} - \Delta R_{ON(MIN)}$.

Note 6: Resistance flatness is defined as the difference between the maximum and minimum on-resistance values, as measured over the specified analog signal range.

Note 7: Leakage parameters are 100% tested at maximum rated temperature, and guaranteed by correlation at TA = +25°C.

Note 8: Off-isolation = 20log10 [V_{COM} / (V_{NC} or V_{NO})], V_{COM} = output, V_{NC} or V_{NO} = input to off switch.

Note 9: Between any two switches.

Note 10: Leakage testing for single-supply operation is guaranteed by testing with dual supplies.

Typical Operating Characteristics $(V + = +5V, V - = -5V, GND = 0V, T_A = +25$ °C, unless otherwise noted.) ON-RESISTANCE vs. V_{COM} ON-RESISTANCE vs. V_{COM} AND ON-RESISTANCE vs. V_{COM} (DUAL SUPPLIES) **TEMPERATURE (DUAL SUPPLIES)** (SINGLE SUPPLY) 180 350 110 V+ V- = 2 0V V + = 2.7V160 100 300 140 90 250 120 = 3.0V 80 R_{ON} (Ω) **3** 200 <u>ම</u> 100 T_A = +85°C 70 80 150 60 60 100 V+, V- = 4.0V 50 40 V+, V- = 5.0V50 40 20 -55° 30 0 -3 -2 -5 -4 0 -5 -4 0 0 V_{COM} (V) V_{COM} (V) V_{COM} (V) ON- AND OFF-LEAKAGE CURRENT **CHARGE INJECTION** ON-RESISTANCE vs. V_{COM} AND **TEMPERATURE (SINGLE SUPPLY)** vs. TEMPERATURE vs.V_{COM} 10n 200 180 1n ON LEAKAGE 160 LEAKAGE (A) 100p (G) 140 NO 120 V + = +5VO (pc) +85°C 0 V- = 0V 120 10p 100 OFF LEAKAGE 1p 80 T_A = -55°C -2 0.1p 60 -4 -3 -2 -5 -1 0 1 0 2 3 -25 0 50 75 -55 25 $V_{COM}(V)$ TEMPERATURE (°C) V_{COM} (V) TURN-ON/OFF TIME POWER-SUPPLY CURRENT TURN-ON/OFF TIME vs. vs. TEMPERATURE vs. TEMPERATURE SUPPLY VOLTAGE 200 100 90 180 80 0.1 160 140 70 (us) 60 I- (µA) 0.01 120 ton toFF 50 100 ± 0.001 ξ 40 80 ton 30 60 toff 20 0.0001 40 toff 10 20 0 0.00001 100 25 50 -55 10 11 12

TEMPERATURE (°C)

V+ (V)

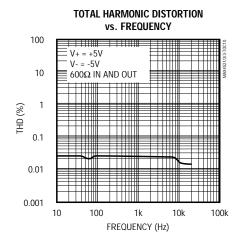
6

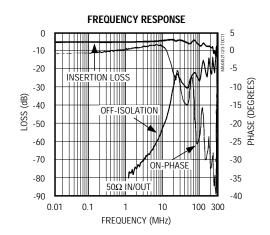
TEMPERATURE (°C)

M/IXI/N

_Typical Operating Characteristics (continued)

 $(V+=+5V, V-=-5V, GND=0V, T_A=+25^{\circ}C, unless otherwise noted.)$





Pin Description

	PIN		NAME	FUNCTION		
MAX4521	MAX4522	MAX4523	IVAIVIL	FONCTION		
1, 16, 9, 8	1, 16, 9, 8	1, 16, 9, 8	IN1-IN4	Logic-Control Digital Inputs		
2, 15, 10, 7	2, 15, 10, 7	2, 15, 10, 7	COM1-COM4	Analog Switch Common* Terminals		
3, 14, 11, 6	_	_	NC1-NC4	Analog Switch Normally Closed Terminals		
_	3, 14, 11, 6	_	NO1-NO4	Analog Switch Normally Open Terminals		
_	_	3, 6	NO1, NO4	Analog Switch Normally Open Terminals		
_	_	14, 11	NC2, NC3	Analog Switch Normally Closed Terminals		
4	4	4	V-	Negative Analog Supply-Voltage Input. Connect to GND for single-supply operation.		
5	5	5	GND	Ground. Connect to digital ground. (Analog signals have no ground reference; they are limited to V+ and V)		
12	12	12	N.C.	No Connect. Not internally connected.		
13	13	13	V+	Positive Analog and Digital Supply Voltage Input. Internally connected to substrate.		

^{*}NO_ (or NC_) and COM_ pins are identical and interchangeable. Either may be considered as an input or output; signals pass equally well in either direction.

_Applications Information

Power-Supply Considerations

Overview

The MAX4521/MAX4522/MAX4523 construction is typical of most CMOS analog switches. They have three supply pins: V+, V-, and GND. V+ and V- are used to drive the internal CMOS switches, and they set the limits of the analog voltage on any switch. Reverse ESD-protection diodes are internally connected between each analog-signal pin and both V+ and V-. If any analog signal exceeds V+ or V-, one of these diodes conducts. During normal operation these reverse-biased ESD diodes leak, forming the only current drawn from V+ or V-.

Virtually all the analog leakage current is through the ESD diodes. Although the ESD diodes on a given signal pin are identical and therefore fairly well balanced, they are reverse biased differently. Each is biased by either V+ or V- and the analog signal. This means their leakages vary as the signal varies. The difference in the two diode leakages from the signal path to the V+ and V- pins constitutes the analog-signal-path leakage current. All analog leakage current flows to the supply terminals, not to the other switch terminal. This explains how both sides of a given switch can show leakage currents of the same or opposite polarity.

There is no connection between the analog-signal paths and GND. The analog-signal paths consist of an N-channel and P-channel MOSFET with their sources and drains paralleled, and their gates driven out of phase to V+ and V- by the logic-level translators.

V+ and GND power the internal logic and logic-level translators, and set the input logic thresholds. The logic-level translators convert the logic levels to switched V+ and V- signals, to drive the gates of the analog switches. This drive signal is the only connection between the logic supplies and the analog supplies. V+ and V- have ESD-protection diodes to GND. The logic-level inputs and output have ESD protection to V+ and to GND.

Increasing V- has no effect on the logic-level thresholds, but it does increase the drive to the P-channel switches, reducing their on-resistance. V- also sets the negative limit of the analog-signal voltage.

The logic-level thresholds are CMOS/TTL compatible when V+=+5V. The threshold increases slightly as V+ is raised, and when V+ reaches +12V, the level threshold is about 3.1V. This is above the TTL output high-level minimum of 2.8V, but still compatible with CMOS outputs.

Bipolar Supplies

The MAX4521/MAX4522/MAX4523 operate with bipolar supplies between $\pm 2V$ and $\pm 6V$. The V+ and V- supplies need not be symmetrical, but their sum cannot exceed the absolute maximum rating of 13.0V. **Do not connect the MAX4521/MAX4522/MAX4523 V+ to +3V, and then connect the logic-level-input pins to TTL logic-level signals. TTL logic-level outputs in excess of the absolute maximum ratings can damage the part and/or external circuits.**

Caution: The absolute maximum V+ to V- differential voltage is 13.0V. Typical ± 6 V or 12V supplies with $\pm 10\%$ tolerances can be as high as 13.2V. This voltage can damage the MAX4521/MAX4522/MAX4523. Even $\pm 5\%$ tolerance supplies may have overshoot or noise spikes that exceed 13.0V.

Single Supply

The MAX4521/MAX4522/MAX4523 operate from a single supply between +2V and +12V when V- is connected to GND. All of the bipolar precautions must be observed.

High-Frequency Performance

In 50Ω systems, signal response is reasonably flat up to 50MHz (see *Typical Operating Characteristics*). Above 20MHz, the on-response has several minor peaks that are highly layout dependent. The problem with high-frequency operation is not turning the switch on, but turning it off. The off-state switch acts like a capacitor and passes higher frequencies with less attenuation. At 10MHz, off-isolation is about -52dB in 50Ω systems, becoming worse (approximately 20dB per decade) as frequency increases. Higher circuit impedances also make off-isolation worse. Adjacent channel attenuation is about 3dB above that of a bare IC socket, and is due entirely to capacitive coupling.

Test Circuits/Timing Diagrams

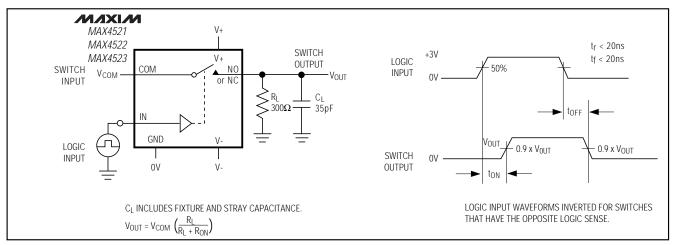


Figure 1. Switching Time

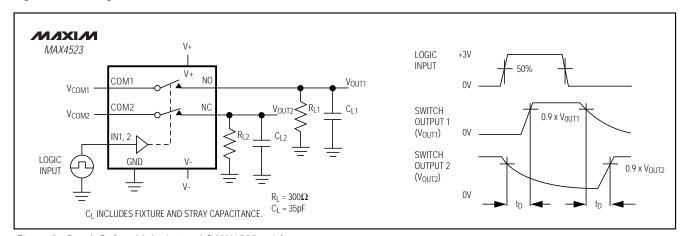


Figure 2. Break-Before-Make Interval (MAX4523 only)

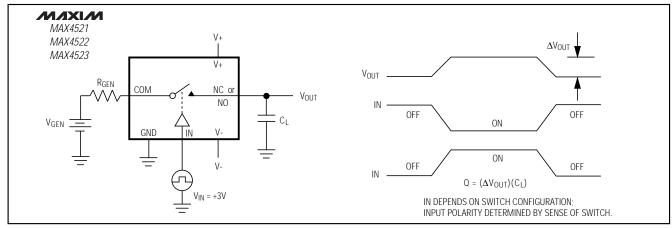


Figure 3. Charge Injection

Test Circuits/Timing Diagrams (continued)

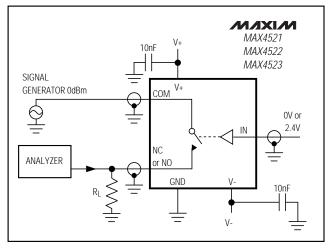


Figure 4. Off Isolation

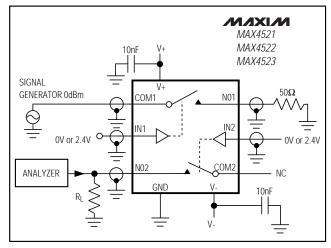


Figure 5. Crosstalk

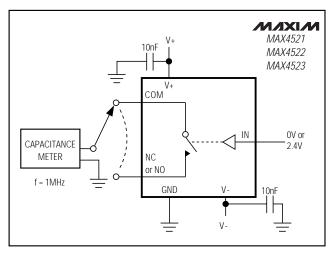


Figure 6. Channel-Off Capacitance

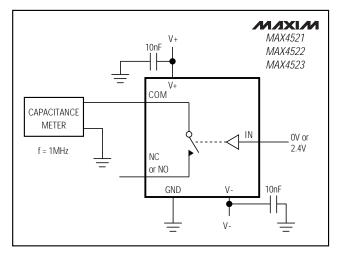
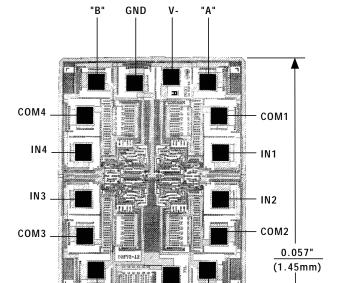


Figure 7. Channel-On Capacitance

_Ordering Information (continued)

PART	TEMP. RANGE	PIN-PACKAGE
MAX4521EPE	-40°C to +85°C	16 Plastic DIP
MAX4521ESE	-40°C to +85°C	16 Narrow SO
MAX4521EEE	-40°C to +85°C	16 QSOP
MAX4521MJE	-55°C to +125°C	16 CERDIP**
MAX4522CPE	0°C to +70°C	16 Plastic DIP
MAX4522CSE	0°C to +70°C	16 Narrow SO
MAX4522CEE	0°C to +70°C	16 QSOP
MAX4522C/D	0°C to +70°C	Dice*
MAX4522EPE	-40°C to +85°C	16 Plastic DIP
MAX4522ESE	-40°C to +85°C	16 Narrow SO
MAX4522EEE	-40°C to +85°C	16 QSOP
MAX4522MJE	-55°C to +125°C	16 CERDIP**
MAX4523CPE	0°C to +70°C	16 Plastic DIP
MAX4523CSE	0°C to +70°C	16 Narrow SO
MAX4523CEE	0°C to +70°C	16 QSOP
MAX4523C/D	0°C to +70°C	Dice*
MAX4523EPE	-40°C to +85°C	16 Plastic DIP
MAX4523ESE	-40°C to +85°C	16 Narrow SO
MAX4523EEE	-40°C to +85°C	16 QSOP
MAX4523MJE	-55°C to +125°C	16 CERDIP**

^{*}Contact factory for dice specifications.



Chip Topography

МАХ	(4521	МАХ	MAX4522		(4523
PIN	NAME	PIN	PIN NAME		NAME
А	NC1	А	NO1	А	NO1
В	NC4	В	NO4	В	NO4
С	NC3	С	NO3	С	NC3
D	NC2	D	NO2	D	NC2

۷+

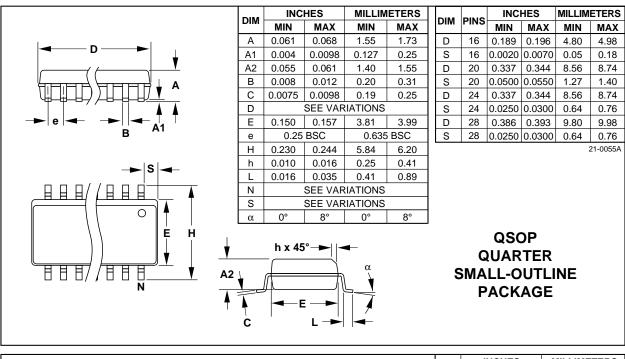
0.046" (1.19mm) "D"

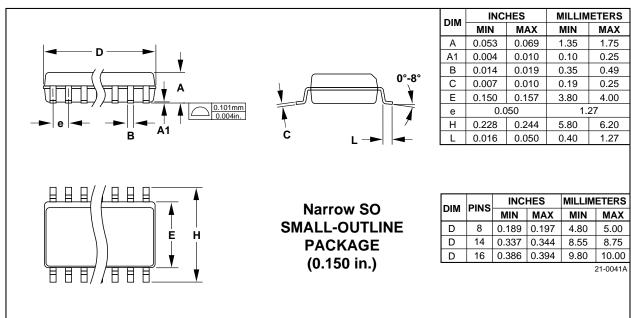
TRANSISTOR COUNT: 97
SUBSTRATE CONNECTED TO V+

"C"

^{**}Contact factory for availability.

Package Information





Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.

12 _____Maxim Integrated Products, 120 San Gabriel Drive, Sunnyvale, CA 94086 408-737-7600